

IN THE SPECIFICATION

Please replace the paragraph at page 10, lines 2-17, with the following rewritten paragraph:

Figures 2A and 2B are plan and cross-sectional views, respectively, of a resonance type optical modulator comprising a modulation electrode formed on an optical path for applying an electric field to the optical path, and a common electrode formed in opposition to the modulation electrode, in which the modulation electrode comprises an open-ended, microwave asymmetric coplanar waveguide. The resonance type modulator shown is a Mach-Zehnder interferometer type optical modulator used for intensity-modulating a light wave having a wavelength of 1.55 microns, using a microwave signal having a center frequency of 10 GHz. The modulator has a z-cut LiNbO₃ substrate in which an optical path 10, 11, 12 is formed by thermally diffusing Ti (titanium) into the substrate. To suppress the attenuation of the light propagating in the optical waveguide, a layer 9 of silicon oxide having a thickness of 0.55 μm is formed on the substrate. A metal layer (gold, a thickness of 2 μm) is provided on the layer 9 to form thereon a modulation electrode, a transformer, stubs and a common electrode.